IN THE SPECIFICATION:

Please replace paragraph number **[0001]** with the following rewritten paragraph:

[0001] This application is a divisional of application Serial No. 09/921,615, filed August 3, 2001, ~~pending~~ now U.S. Patent 6,632,736, issued October 14, 2003, which is a continuation of application Serial No. 09/495,534, filed January 31, 2000, now U.S. patent 6,291,340, issued September 18, 2001, which is a continuation of application Serial No. 09/012,685, filed January 23, 1998, now U.S. Patent 6,081,034, issued June 27, 2000, which is a continuation of application Serial No. 08/509,708, filed July 31, 1995, now U.S. Patent 5,723,382, issued March 3, 1998, which is a continuation-in-part of U.S. application 08/228,795, filed April 15, 1994, now abandoned, which is a continuation of now abandoned U.S. application 07/898,059, filed June 12, 1992.

Please replace paragraph number **[0025]** with the following rewritten paragraph:

[0025] Still referring to FIG. 1, the carrier gas, at least partially saturated with a vaporized precursor compound, is transported via a primary intake manifold 17 to a premix chamber 18. Additional carrier gas may be optionally supplied to premix chamber 18 via supply tube 19. Carrier gas, mixed with the precursor compound, is then ducted through a secondary intake manifold 20 to a shower head 21, from which they enter the chamber 11. The precursor compound, upon coming into contact with the heated wafer, pyrolyzes and deposits as a highly conformal titanium carbonitride film on the surface of the wafer 12. The reaction products from the pyrolysis of the precursor compound are withdrawn from the chamber 11 via an exhaust manifold 22. Incorporated in the exhaust manifold 22 are a pressure sensor 23, a pressure switch 24, a vacuum valve 25, a pressure control valve 26, a blower 27, and a particulate filter 28, which filters out solid reactants before the exhaust is vented to the atmosphere. During the deposition process, the pressure within chamber 11 is maintained at a pressure of less than 100 torr and at a pressure of less than 1 torr by pressure control components 23, 24, 25, 26, and 27. The process parameters that are presently deemed to be optimum, or nearly so, are a carrier

gas flow through secondary intake manifold 20 of 400 standard cubic centimeters per minute (scc/m), a deposition chamber temperature of 425°C, and a flow of carrier gas through bubbler apparatus 16 of 100 scc/m, with the liquid ~~precursor material~~ tetrakis-dialkylamido-titanium 15 being maintained at a constant temperature of approximately 40°C.